

N-Channel 300 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (mΩ) (Typ.)	I _D (A) ^a	Q _g (Typ.)		
300	210 at V _{GS} = 10 V	13	26.5 nC		

Din-Tek SEMICONDUCTOR

FEATURES

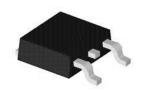
- DT-Trench Power MOSFET
- 100 % Rg and UIS tested
- · Fast Switching
- · avalanche tested

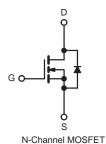
APPLICATIONS

· High frequency switching mode power supply

TO-252 Pin Configuration

Top View





ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	LIMIT	UNIT				
Drain-Source Voltage	V _{DS}	300	V				
Gate-Source Voltage	V _{GS}	± 30	V				
Continuous Drain Current (T _J = 150 °C) ^a	T _C = 25 °C	I _D	13	А			
Continuous Diam Current (1) = 130 °C)	T _C = 100 °C	ıD	8.2				
Pulsed Drain Current ^b	I _{DM}	52					
Single Avalanche Energy	E _{AS}	550	mJ				
Maximum Dawar Dissination C	T _C = 25 °C	D.	115	W			
Maximum Power Dissipation ^c	T _C = 100 °C	P _D	46.3] vv			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to +150	°C			

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) d	R _{thJA}	62	°C/W			
Junction-to-Case (Drain)	R_{thJC}	1.08				

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{8JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



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PARAMETER SYM		TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	300	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 30 \text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current		V _{DS} = 300 V, V _{GS} = 0 V	=	-	1	μΑ
	I _{DSS}	V _{DS} =240 V, V _{GS} = 0 V, T _J = 125 °C	-	-	100	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	13	-	-	Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 6.5 A	-	210	250	mΩ
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_{D} = 6.5 \text{ A}$	-	15	-	S
Dynamic ^b						
Input Capacitance	C _{iss}		-	1300	-	pF
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	-	140	-	
Reverse Transfer Capacitance	C _{rss}		-	4.5	-	
Total Gate Charge ^c	Qg		-	26.5	-	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 240 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}$	-	8.8	-	nC
Gate-Drain Charge ^c	Q_{gd}		-	6.5	-	
Gate Resistance	R _g	f = 1 MHz	-	2.3	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	26	-	
Rise Time ^c	t _r	$V_{DD} = 150 \text{ V}, I_D = 14 \text{ A}, R_g = 15 \Omega$	-	27.5	-	ns
Turn-Off Delay Time ^c	t _{d(off)}	V _{GS} = 10 V	-	44.5	-	
Fall Time ^c	t _f		-	16	-	
Drain-Source Body Diode Ratings and	Characterist	ics ^b (T _C = 25 °C)				
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	13	Α
Pulsed Current	I _{SM}		-	-	52	Α
Forward Voltage ^a	V_{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1.2	V
Reverse Recovery Time	t _{rr}	1 12 A di/dt = 100 A/···	-	168	-	ns
Reverse Recovery Charge	Q_{rr}	I _F = 13 A, di/dt = 100 A/μs	-	1.1	-	μC

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

Figure 1 Typical Output Characteristics

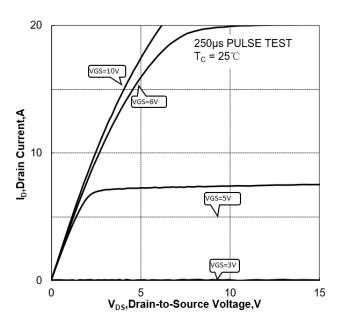


Figure 2 Typical Transfer Characteristics

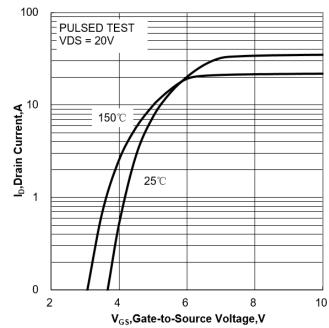


Figure 3 Typical Drain to Source ON Resistance vs Drain Current

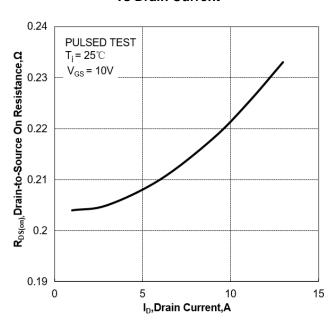
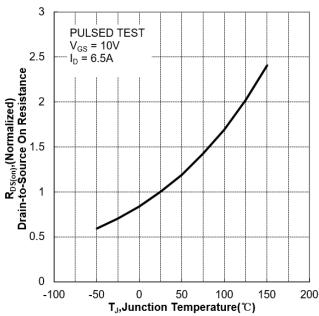


Figure 4 Typical Drian to Source on Resistance vs Junction Temperature





TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

Figure 5 Typical Theshold Voltage vs Junction Temperature

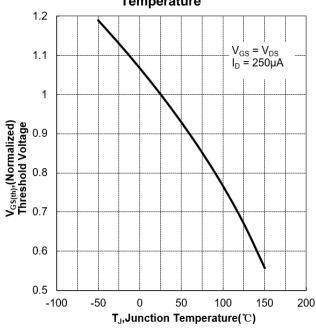


Figure 6 Typical Breakdown Voltage vs Junction Temperature

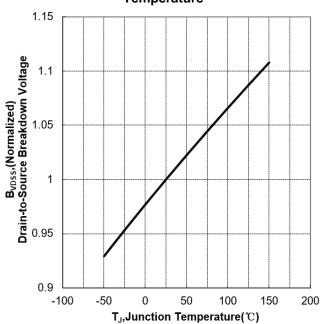


Figure 7 Typical Theshold Voltage vs Junction Temperature

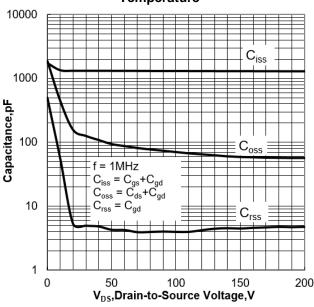
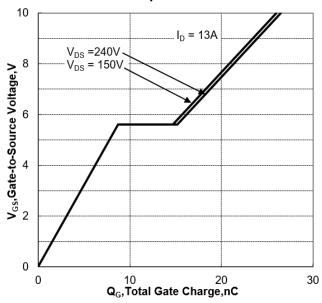
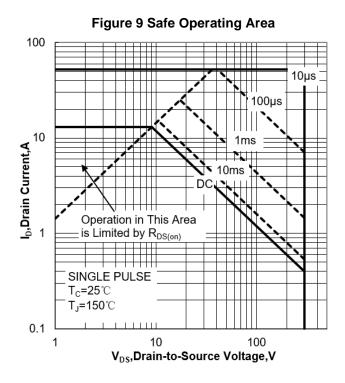


Figure 8 Typical Breakdown Voltage vs Junction Temperature





TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)



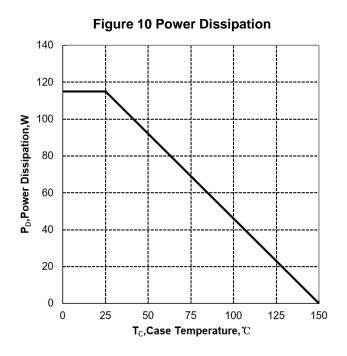
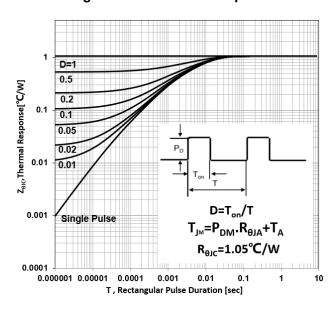
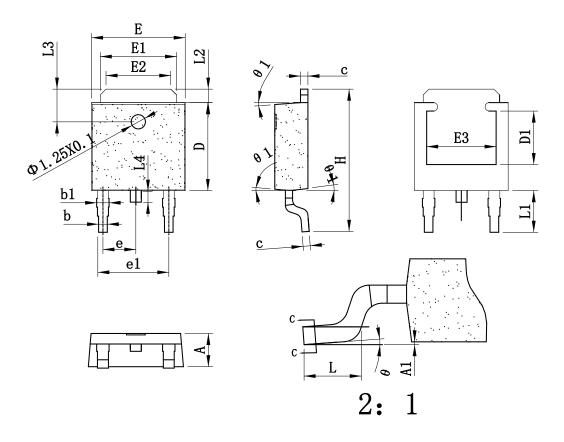


Figure 11 Max Thermal Impendance



TO-252-2L PACKAGE OUTLINE



SYMBOL	mm			SYMBOL	mm		
	MIN	TYP	MAX	STWIDOL	MIN	TYP	MAX
Α	2.20	2.30	2.40	E3	4.80 REF		
A1	1.00	1.07	1.28	е	2.286 REF		
b	0.55	0.60	0.65	e1	4.57REF		
b1	0.70	0.80	0.90	Н	10.00	10.20	10.40
С	0.47	0.52	0.57	L	9.15	9.35	9.55
D	6.00	6.10	6.20	L1	2.95	3.05	3.15
D1	3.70 REF		L2	0.88	0.93	0.98	
E	6.45	6.55	6.65	L3	2.20	2.26	2.31
E1	5.20	5.30	5.40	θ	0°	2°	5°
E2	4.40	4.50	4.60	θ1	5°	7°	9°

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